

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	OverallWafer Secondary Flat	None	
	5.0	Overall Thickness	521.00 +/- 11.00 $\mu$ m	ADE, 100%
	6.0	LPDs > 0.3 $\mu$ m	<30	Tencor Particle counter
	7.0	Frontsurface condition	Polished, roughness <5A	Guaranteed by process
	8.0	Total Thickness Variation (TTV)	<5.00 $\mu$ m	Guaranteed by Process
	9.0	Bow	<60.00 $\mu$ m	ADE to ASTM F534, 100%
	10.0	Warp	<60.00 $\mu$ m	
	11.0	Edge Chips	0	Bright Light, 100%
	12.0	Edge Exclusion	5mm	
	13.0	Lasermarking	On wafer BACKSIDE	Guaranteed by process
14.0	Wafer Oxygen concentration	<28 ppm	Wafer Vendor	
15.0	Radial Resistivity Gradient	<=10%	Wafer Vendor	
16.0	Silicon Dislocation Etch Pit Density	<= 100/cm <sup>2</sup>	Wafer Vendor	
HandleSilicon	17.0	Handle Growth Method	CZ	Wafer Vendor
	18.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	19.0	Handle Thickness	500.00 +/- 10.00 $\mu$ m	ADE, 100%
	20.0	Handle Doping Type	N	Wafer Vendor
	21.0	Handle Dopant	Any	Wafer Vendor
	22.0	Handle Resistivity	1 ~ 10 Ohmcm	Wafer Vendor
	23.0	Backside Finish	Polished with lasermark and oxide	Wafer Vendor
BuriedOxide	24.0	Oxide Type	Thermal	
	25.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	26.0	Oxide formed on	Handle	
DeviceSilicon	27.0	Device Growth Method	CZ	Wafer Vendor
	28.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	29.0	Nominal Thickness	20.00 +/- 1.00 $\mu$ m	Filmetrics, 100% 9-Pt (note3)
	30.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	31.0	Device Doping Type	N	Wafer Vendor
	32.0	Device Dopant	Any	Wafer Vendor
	33.0	Device Resistivity	1 ~ 10 Ohmcm	Wafer Vendor
	34.0	Voids	none	IR Inspection, 100%
	35.0	Scratches	0	Bright Light, 100% (note 2)

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Category

Parameter

Specification

Measurement Method

DeviceSilicon

36.0

Haze

none

Bright Light, 100% (note 2)

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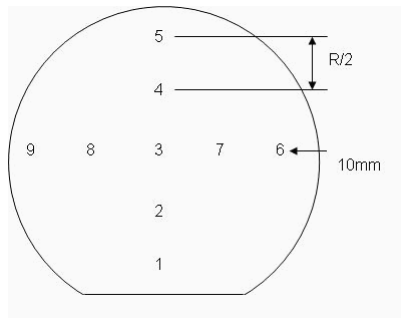
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information